

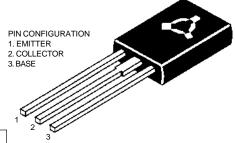


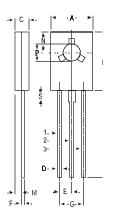
## TO-126 (SOT-32) Plastic Package

**CSA715** 

# CSA715 PNP PLASTIC POWER TRANSISTOR

Complementary to CSC1162 Low frequency Power Amplifier





DIM	MIN.	MAX.	
A	7.4	7.8	
Ð	10.5	10.8	
С	2.4	2.7	
D	0.7	0.9	
Е	2.25 TYP.		
F	0.49	0.75	
G	4.5	TYP.	
L	15.7	TYP.	
M	1.27	TYP.	
N	3.75	TY <b>P</b> .	
P	3.0	3.2	
\$	2.5	TYP.	

ALL DIMENSIONS IN MM

#### ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)	$V_{CBO}$	max.	35 V
Collector-emitter voltage (open base)	$V_{C\!E\!O}$	max.	35 V
Collector current	$I_C$	max.	2.5 A
Total power dissipation up to $T_C = 25^{\circ}C$	$P_{tot}$	max.	10 W
Junction temperature	$T_{i}$	max.	150 °C
Collector-emitter saturation voltage	J		
$I_C = 2 A$ ; $I_B = 0.2 A$	$V_{CEsat}$	max.	1.0 V
D.C. current gain			
$I_C = 0.5 \text{ A}; V_{CE} = 2 \text{ V}$	$h_{\!F\!E}$	min.	60
		max.	320
	10 B		

### **RATINGS** (at $T_A$ =25°C unless otherwise specified)

Limiting values			
Collector-base voltage (open emitter)	$V_{CBO}$	max.	35 V
Collector-emitter voltage (open base)	$V_{C\!E\!O}$	max.	35 V
Emitter-base voltage (open collector)	$V_{EBO}$	max.	5.0 V
Collector current	$I_C$	max.	2.5 A

Collector current (Peak value)	$I_C$	max.	3	$\boldsymbol{A}$
Total power dissipation up to $T_A = 25^{\circ}C$	$P_{tot}$	max.	0.75	W
Total power dissipation up to $T_C = 25^{\circ}C$	$P_{tot}$	max.	10	W
Junction temperature	$T_{j}$	max.	<i>150</i>	${}^{o}C$
Storage temperature	$T_{stg}$	-65 to	+150	°C
CHARACTERISTICS				
$T_{amb} = 25$ °C unless otherwise specified				
Collector cutoff current				
$I_E = 0$ ; $V_{CB} = 35 V$	$I_{CBO}$	max.	20	$\mu A$
Breakdown voltages				
$I_C = 10 \text{ mA}; I_B = 0$	$V_{C\!E\!O}$	min.	35	V
$I_C = 1 \text{ mA}; I_E = 0$	$V_{C\!BO}$	min.	35	V
$I_E = 1 \text{ mA}; I_C = 0$	$V_{EBO}$	min.	5	V
Saturation voltage				
$I_C = 2 A$ ; $I_B = 0.2 A$	$V_{CEsat}$	max.	1.0	V
Base-emitter on voltage				
$I_C = 1.5 A; V_{CE} = 2 V$	$V_{BE(on)}$	max.	1.5	V
D.C. current gain	22(01)			
$I_C = 0.5 \text{ A}; V_{CF} = 2 V^{**}$	$h_{\!F\!E}$	min.	60	
, 62	12	max.	320	
$I_C = 1.5 A; V_{CE} = 2 V (Pulse)$	$h_{FE}$	min.	20	
Transition frequency	11			
$I_C = 0.2 \text{ A}; V_{CE} = 2 \text{ V}$	$f_T$	typ.	160	MHz

<sup>\*\*</sup> hfe classification: B: 60-120 C: 100-200 D: 160-320

### **Customer Notes**

#### **Disclaimer**

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